

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L4	120612	provid\$3 near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:30
L5	16987	appl\$3 near3 resist same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:33
L6	7725	structure near3 coupl \$3 same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:34
L7	72	L5 and L6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:34
L8	26	L4 and L7	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:35
L9	2941	deposit\$3 near3 solution same semiconductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:38
L10	4	deposit\$3 near3 solution near3 semiconductor same depression	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:41

L11	0	L8 and L10	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:42
L12	0	L8 and L9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:43
L13	482	resist near3 structure same coupl\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:48
L14	54	deposit\$3 near3 solution same semiconductor with precursor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:50
L15	0	L8 and L14	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 09:51
L17	2211	438/780	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 10:44
L18	879	257/642	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 10:44
L19	185	L17 and L18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 10:44

L20	2514	438/758	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 10:53
L21	15	257/E21.299	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 10:53
L22	0	L20 and L21	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 10:53
L23	115	resist\$3 near3 structure with coupl\$3 same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 11:01
L24	7408	resist\$3 near3 structure same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 11:01
L25	115	L23 and L24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 11:01
L26	9795	protrus\$3 same depress \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 11:01
L27	2	L26 and L25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/16 11:01

L34	4	("20040021810" "4791302").pn.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/09/16 11:03
S1	3294	resist near3 structure same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:20
S2	2	("6416778").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:23
S3	11	depression same deposit\$3 near3 solution same protrusion	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:25
S4	3	S1 and S3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:26
S5	0	tough near3 align\$3 same depression	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:27
S6	11489	protrusion same depression	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:27
S7	11	S1 and S6	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:27

S8	3	S7 and S3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:28
S9	120413	provid\$3 near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:29
S10	1	resist near3 structure with couple same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:29
S11	115	resist\$3 near3 structure with coupl\$3 same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:30
S13	7394	resist\$3 near3 structure same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:31
S14	115	S11 and S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:31
S15	2	S6 and S14	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:32
S16	9773	protrus\$3 same depress \$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 12:32

S18	49	("5622633" "4543592" "4566940" "5317177" "5319246" "5358881" "5376572" "5424233" "5470778" "5500384" "5514890" "5576569" "5635740" "5668410" "5726499" "5756396" "5792707" "6025246" "6051885" "6063702" "6064084" "6187671" "6191001" "6225148" "6225148" "6268263" "6274434" "6333232" "6451688" "6639296" "6821805" "6828648" "20010031559" "20020197800" "20040041231" "20040192060" "20060281332" "20070093027" "20070096096" "4125418" "4503334" "4791302" "4903112" "5233212" "5252414" "5320932" "5338699" "5429967" "5494857" "5598013").pn.	US-PGPUB; USPAT	OR	ON	2008/09/09 15:41
S19	49	("5622633" "4543592" "4566940" "5317177" "5319246" "5358881" "5376572" "5424233" "5470778" "5500384" "5514890" "5576569" "5635740" "5668410" "5726499" "5756396" "5792707" "6025246" "6051885" "6063702" "6064084" "6187671" "6191001" "6225148" "6225148" "6268263" "6274434" "6333232" "6451688" "6639296" "6821805" "6828648" "20010031559" "20020197800" "20040041231" "20040192060" "20060281332" "20070093027" "20070096096" "4125418" "4503334" "4791302" "4903112" "5233212" "5252414"	US-PGPUB; USPAT; USOCR	OR	ON	2008/09/09 15:41

		"5320932" "5338699" "5429967" "5494857" "5598013").pn.				
S20	11489	protrusion same depression	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:01
S21	3	S18 and S20	US-PGPUB; USPAT; USOCR	OR	ON	2008/09/09 16:01
S22	120413	provid\$3 near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:03
S23	9	S18 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:03
S24	115	resist\$3 near3 structure with coupl\$3 same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:04
S25	1	S18 and S24	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:04
S26	3294	resist near3 structure same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:06
S27	1	S19 and S26	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:06

S28	11	depress\$3 same deposit \$3 near3 solution same protrus\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/09 16:12
S29	120413	provid\$3 near3 substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 09:44
S30	618	appl\$3 near3 resist near3 structure	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:10
S31	181	appl\$3 near3 resist near3 structure same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:10
S32	181	S30 and S31	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:11
S33	0	appl\$3 near3 resist near3 structure with couple same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:11
S34	69	resist near3 structure same couple	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:12
S35	21	S29 and S32	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:12



S36	0	S34 and S35	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:13
S37	2	S29 and S34	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2008/09/10 10:13

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